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S/N Unknown

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Gurtej Singh Sandhu et al.

Examiner: Unknown

Serial No.: 09/652,619

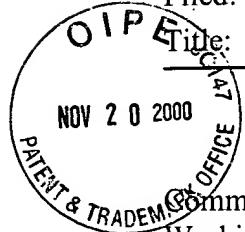
Group Art Unit: Unknown

Filed: August 31, 2000

Docket: 303.085US4

Title:

METHOD FOR FORMING A METALLIZATION LAYER



**SUPPLEMENTAL PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

When the above-identified patent application is taken up for consideration, please amend the application as follows:

**IN THE CLAIMS**

Please cancel claim 1 without prejudice, and add new claims 21-54 as follows.

- B1*  
*Chk*
21. (New) An integrated circuit, comprising:  
a substrate;  
a first layer of material formed on the substrate, the first layer having contact vias extending through to the substrate;  
a second layer formed on the first layer, the second layer lining the contact vias; and  
a metallization layer on the second layer.
22. (New) The integrated circuit of claim 21, wherein the metallization layer comprises non-alloy copper.
23. (New) The integrated circuitry of claim 21, wherein the metallization layer fills the contact vias.
24. (New) The integrated circuitry of claim 21, wherein the first layer has a first surface potential and the second layer has a second surface potential, and wherein the first surface potential is lower than the second surface potential.

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01 FC:103  
02 FC:102

252.00 OP  
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